

EMB2 / UMB2N / IMB2A

PNP -100mA -50V Complex Digital Transistors (Bias Resistor Built-in Transistors) Datasheet

Parameter	Tr1 and Tr2
V _{CC}	-50V
I _{C(MAX.)}	-100mA
R ₁	47 kΩ
R ₂	47 kΩ

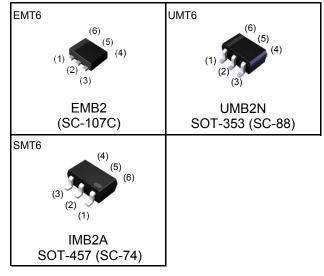
Features

- 1) Built-In Biasing Resistors, $R_1 = R_2 = 47k\Omega$.
- 2) Two DTA144E chips in one package.
- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see inner circuit).
- 4) The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input. They also have the advantage of completely eliminating parasitic effects.
- 5) Only the on/off conditions need to be set for operation, making the circuit design easy.
- 6) Lead Free/RoHS Compliant.

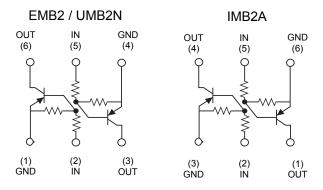
Application

Inverter circuit, Interface circuit, Driver circuit

•Outline



Inner circuit



Packaging specifications

Part No.	Package	Package size (mm)	Taping code	Reel size (mm)	Tape width (mm)	Basic ordering unit (pcs)	Marking
EMB2	EMT6	1616	T2R	180	8	8,000	B2
UMB2N	UMT6	2021	TN	180	8	3,000	B2
IMB2A	SMT6	2928	T110	180	8	3,000	B2

●Absolute maximum ratings (Ta = 25°C)

<For Tr1 and Tr2 in common>

Para	Parameter		Values	Unit
Supply voltage		V _{CC}	-50	V
Input voltage		V _{IN}	-40 to +10	V
Output current		Ι _ο	-30	mA
Collector current		^{*1} ا _{C(MAX.)}	-100	mA
Power dissipation	EMB3 / UMB3N	$- P_{\rm D}^{*2}$	150 (Total) ^{*3}	mW
ІМВЗА			300 (Total) ^{*4}	mW
Junction temperature		Tj	150	°C
Range of storage temperature		T _{stg}	-55 to +150	°C

•Electrical characteristics(Ta = 25°C)

<For Tr1 and Tr2 in common>

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input voltage	V _{I(off)}	$V_{CC} = -5V, I_{O} = -100 \mu A$	-	-	-0.5	V
Input voltage	V _{I(on)}	$V_0 = -0.3V, I_0 = -2mA$	-3.0	-	-	v
Output voltage	V _{O(on)}	I _O / I _I = -10mA / -0.5mA	-	-0.1	-0.3	V
Input current	I _I	V ₁ = -5V	-	-	-0.18	mA
Output current	I _{O(off)}	$V_{CC} = -50V, V_1 = 0V$	-	-	-0.5	μA
DC current gain	Gı	$V_0 = -5V, I_0 = -5mA$	68	-	-	-
Input resistance	R ₁	-	32.9	47	61.1	kΩ
Resistance ratio	R_2/R_1	-	0.8	1	1.2	-
Transition frequency	f _T *1	V _{CE} = -10V, I _E = 5mA, f = 100MHz	-	250	-	MHz

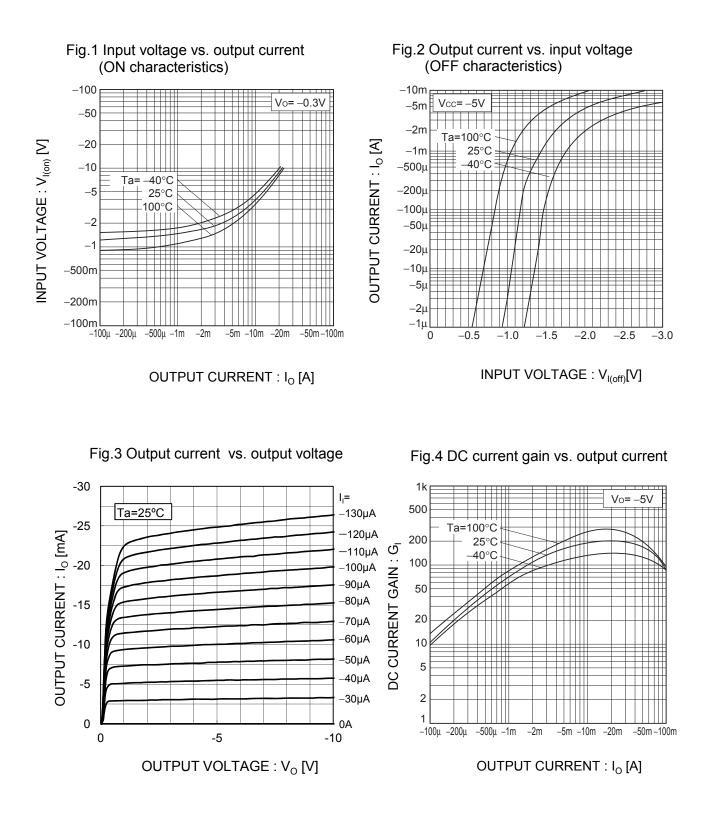
*1 Characteristics of built-in transistor

*2 Each terminal mounted on a reference footprint

*3 120mW per element must not be exceeded.

*4 200mW per element must not be exceeded.

•Electrical characteristic curves(Ta = 25°C)



•Electrical characteristic curves(Ta = 25°C)

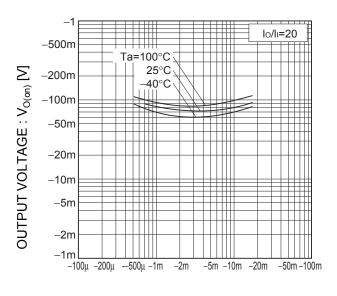
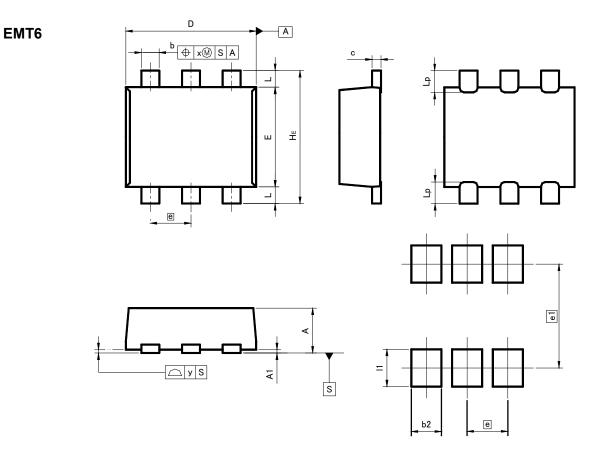


Fig.5 Output voltage vs. output current

OUTPUT CURRENT : Io [A]



•Dimensions (Unit : mm)



Patterm of terminal position areas

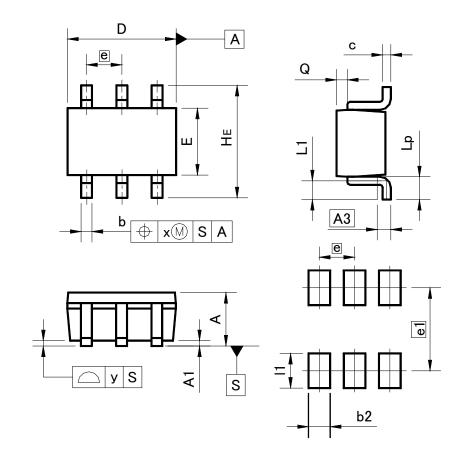
DIM	MILIM	MILIMETERS		HES	
DIN	MIN	MAX	MIN	MAX	
A1	0.00	0.10	0	0.004	
А	0.45	0.55	0.018	0.022	
b	0.17	0.27	0.007	0.011	
с	0.08	0.18	0.003	0.007	
D	1.50	1.70	0.059	0.067	
E	1.10	1.30	0.043	0.051	
е	0.	50	0.02		
HE	1.50	1.70	0.059	0.067	
L	0.10	0.30	0.004	0.012	
Lp	_	0.35	_	0.014	
х	-	0.10	_	0.004	
У	_	0.10	_	0.004	

DIM	MILIMETERS		INC	HES	
DIN	MIN MAX		MIN	MAX	
e1	1.25		0.049		
b2	-	0.37	-	0.015	
1	-	0.45	-	0.018	

Dimension in mm/inches

•Dimensions (Unit : mm)

UMT6



Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES	
DIN	MIN	MAX	MIN	MAX	
А	0.80	1.00	Ι	0.039	
A1	0.00	0.10	0	0.004	
A3	0.	25	0.0	01	
b	0.15	0.30	0.006	0.012	
С	0.10	0.20	0.004	0.008	
D	1.90	2.10	0.075	0.083	
Е	1.15	1.35	0.045	0.053	
е	0.	65	0.03		
HE	2.00	2.20	0.079	0.087	
L1	0.20	0.50	0.008	0.02	
Lp	0.25	0.55	0.01	0.022	
Q	0.10	0.30	0.004	0.012	
х	_	0.10	_	0.004	
У	_	0.10	_	0.004	

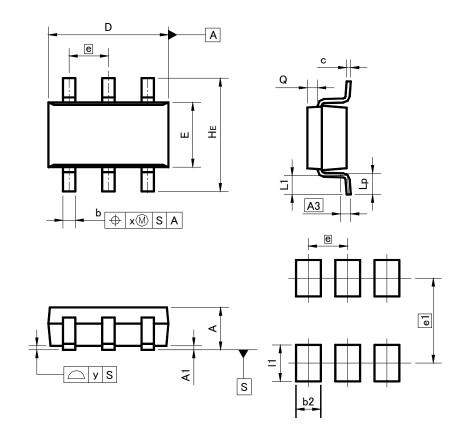
DIM	MILIMETERS		INC	HES	
DIM	MIN MAX		MIN	MAX	
e1	1.55		0.06		
b2	-	0.40	-	0.016	
1	-	0.65	-	0.026	

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Dimension in mm/inches

•Dimensions (Unit : mm)

SMT6



Patterm of terminal position areas

DIM	MILIM	ETERS	INC	HES	
DIM	MIN	MAX	MIN	MAX	
А	1.00	1.30	0.039	0.051	
A1	0.00	0.10	0	0.004	
A3	0.	25	0.0	01	
b	0.25	0.40	0.01	0.016	
С	0.09	0.25	0.004	0.01	
D	2.80	3.00	0.11	0.118	
E	1.50	1.80	0.059	0.071	
е	0.9	95	0.04		
HE	2.60	3.00	0.102	0.118	
L1	0.30	0.60	0.012	0.024	
Lp	0.40	0.70	0.016	0.028	
Q	0.20	0.30	0.008	0.012	
х	_	0.20	_	0.008	
у	-	0.10	-	0.004	

DIM	MILIMETERS		INC	HES	
DIN	MIN MAX		MIN	MAX	
e1	2.10		0.08		
b2		0.60	-	0.024	
1	-	0.90	-	0.035	

Dimension in mm/inches

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